AMENDMENTS TO THE CLAIMS

1-4. (Canceled)

5. (Currently amended) An electronic high frequency switch with a field effect transistor as the switching element, whose switching condition is controlled via the gate voltage fed from a gate voltage source and is controlled by means of a control circuit between a switching on value and switching off value, characterized in that the size of the gate voltage fed from the gate voltage source is selectable between a first voltage and a second voltage by a changeover device depending on the desired linearity or switching speed, wherein neither the first voltage nor the second voltage is a ground voltage.

6. (Previously presented) The high frequency switch according to claim 5, characterized in that the changeover device for the gate voltage is coupled to a correction device in which, for the different gate voltage values, corresponding different correction values for additional high frequency properties of said high frequency switch (transmission or reflection) are stored which, depending on the gate voltage chosen, are used for correcting these additional high frequency properties of said high frequency switch.

7. (Previously presented) An attenuator having a plurality of electronic high frequency switches according to claim 5 or 6, characterized in that the size of the gate voltage of at least some of said high frequency switches are switchable between at least two values.

8. (Previously presented) Attenuator according to claim 7, with a switchable attenuation member connected on the line side, which is controllable with a correction device in which, depending on the frequency of the high frequency signal fed to the attenuator, correction values for compensating for the frequency-dependent junction loss of the electronic high

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frequency switch are stored, characterized in that in the correction device, different frequency response correction values are stored for the different gate voltage values of the high frequency switches and that the changeover device for the gate voltage is coupled to this correction device such that, depending on the selected size of the gate voltage, the respective associated frequency response correction values for controlling the attenuation member connected on the line side are used.

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